

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

 ATTY. DOCKET NO.
061282-0234

 SERIAL NO.
10/574,863

 APPLICANT
Yuichiro SASAKI, et al.

(Substitute for form 1449/PTO)

 FILING DATE
April 06, 2006

 GROUP
2823

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		US 6,153,524	11-28-2000	HENLEY et al.	
		US 6,159,810	12-12-2000	YANG	
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		WO 03/014979 A	02-20-2003	APPLIED MATERIALS, INC.		X
		JP 2530990 B2	09-04-1996	FUJITSU LTD	Corresponds to US 5,407,845	X
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005
		International Search Report issued in International Patent Application No. PCT/JP2004015308 mailed January 18, 2005
		Japanese Notification of Reasons for Refusal, w/ English translation thereof, issued in Japanese Patent Application No. JP 2005-502685 dated May 19, 2009
		European Search Report issued in European Patent Application No. EP 04710478 dated May 12, 2009

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		US 2002/0006689 A1	01-17-2002	MIYASAKA, MITSUTOSHI	

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		BAEK, S., et al., "Characteristics of Low-Temperature Preannealing Effects on Laser-Annealed P/N and N/P Ultra-Shallow Junctions", 2004, pages 54-57, IEEE.
		SEMICONDUCTOR APPLICATIONS, MICROCAVITY ENGINEERING, TRENCH DOPING, pages 662-667
		R. SIEGELE, et al., "Helium Bubbles in silicon: Structure and optical properties," Appl. Phys. Lett. 66 (11), 13 March 1995, pp. 1319-1321
		V.F. REUTOV & A.S. SOKHATSKII, "Helium Ion Bombardment Induced Amorphization of Silicon Crystals," Technical Physics Letters, Vol. 38, No. 7, 2002, pp. 615-617

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